

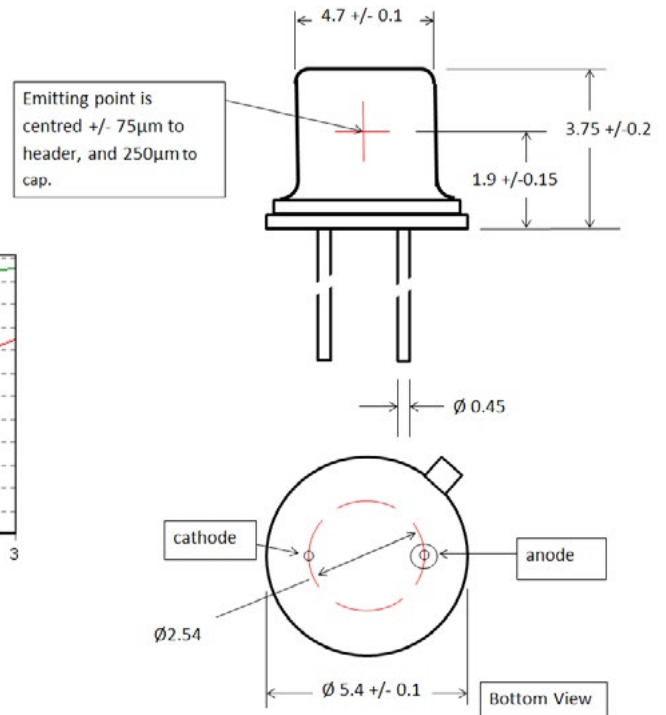
850nm 1.4mW Single Mode VCSEL Laser Diode Type: LCV850SP2

| ELECTRO-OPTICAL CHARACTERISTICS | | | | | | |
|----------------------------------|-------------|----------|------|-----|------|----------------------------|
| T = 25°C unless otherwise stated | | | | | | |
| Parameter | Symbol | Units | Min | Typ | Max | Test Conditions |
| Laser voltage | U_{OP} | V | | | 2.50 | |
| Slope efficiency | η_s | W/A | 0.40 | | | |
| Side mode suppression ratio | SMRS | dB | 10 | | | Output power = 1.4mW |
| Threshold current | I_{TH} | mA | | | 1.50 | |
| EDS damage threshold | | V | 40 | | | Machine model |
| Dynamic polarisation flips | | | | | 0 | |
| Beam divergence | θ | ° | | | 22 | 1/e2; output power = 1.4mW |
| Emission wavelength | λ_E | nm | 845 | | 865 | |
| Differential series resistance | R_S | Ω | 150 | | 250 | |
| Laser current | I_{OP} | mA | | | 3.50 | Output power = 1.4mW |

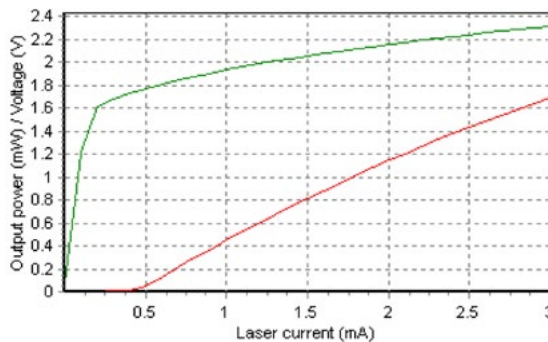


| Absolute Maximum Ratings | |
|----------------------------------|--------------|
| Operating temperature | -20 to 85°C |
| Storage temperature | -40 to 140°C |
| Soldering temperature | 330°C |
| Continuous forward laser current | 4mA |
| Output power | 4mW |
| Continuous reverse current | 10mA |

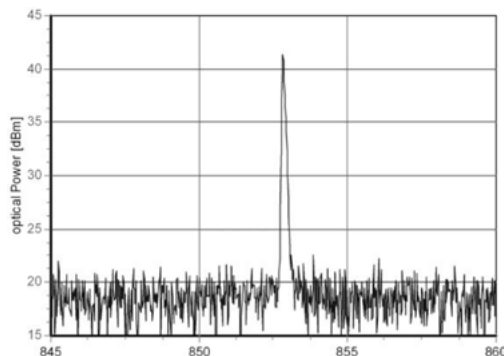
TO dimensions



Electro-optical characteristics



Spectral characteristics



Pin configuration

NOTICE: stresses greater than those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated for extended periods of time may affect device reliability.

ATTENTION: Electrostatic Sensitive Devices
Observe Precautions for Handling

